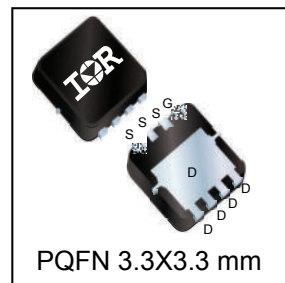
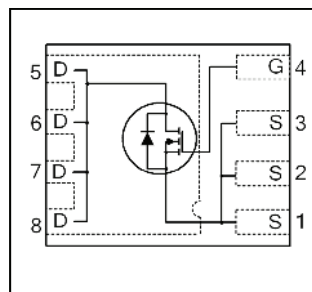


HEXFET® Power MOSFET

V_{DS}	100	V
$R_{DS(on)} \text{ max}$ (@ $V_{GS} = 10V$)	115	mΩ
Q_g (typical)	17	nC
I_D (@ $T_C \text{ (Bottom)} = 25^\circ C$)	11⑥	A



Applications

- POE+ Power Sourcing Equipment Switch

Features

Large Safe Operating Area (SOA)
Low Thermal Resistance to PCB
Low Profile (<1.05mm)
Industry-Standard Pinout
Compatible with Existing Surface Mount Techniques
RoHS Compliant, Halogen-Free
MSL1, Industrial Qualification

results in



Benefits

Increased Ruggedness
Enable better thermal dissipation
Increased Power Density
Multi-Vendor Compatibility
Easier Manufacturing
Environmentally Friendlier
Increased Reliability

Base part number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRFHM3911PbF	PQFN 3.3mm x 3.3mm	Tape and Reel	4000	IRFHM3911TRPbF

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{GS}	Gate-to-Source Voltage	± 20	V
I_D @ $T_A = 25^\circ C$	Continuous Drain Current, V_{GS} @ 10V	3.2	A
I_D @ $T_{C(Bottom)} = 25^\circ C$	Continuous Drain Current, V_{GS} @ 10V	11⑥	
I_D @ $T_{C(Bottom)} = 100^\circ C$	Continuous Drain Current, V_{GS} @ 10V	6.6	
I_D @ $T_C = 25^\circ C$	Continuous Drain Current, V_{GS} @ 10V (Source Bonding Technology Limited)	20⑦	
I_{DM}	Pulsed Drain Current ①	36	W
P_D @ $T_A = 25^\circ C$	Power Dissipation ⑤	2.8	
P_D @ $T_{C(Bottom)} = 25^\circ C$	Power Dissipation	29	
	Linear Derating Factor	0.023	W/°C
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	°C

Notes ① through ⑦ are on page 9

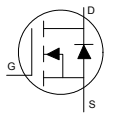
Static @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
BV _{DSS}	Drain-to-Source Breakdown Voltage	100	—	—	V	V _{GS} = 0V, I _D = 250μA
ΔBV _{DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	111	—	mV/°C	Reference to 25°C, I _D = 1mA
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	92	115	mΩ	V _{GS} = 10V, I _D = 6.3A ③
V _{GS(th)}	Gate Threshold Voltage	2.0	—	4.0	V	V _{DS} = V _{GS} , I _D = 35μA
ΔV _{GS(th)}	Gate Threshold Voltage Coefficient	—	-7.6	—	mV/°C	
I _{DSS}	Drain-to-Source Leakage Current	—	—	20	μA	V _{DS} = 100V, V _{GS} = 0V
		—	—	250		V _{DS} = 80V, V _{GS} = 0V, T _J = 125°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V _{GS} = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V _{GS} = -20V
g _{fs}	Forward Transconductance	20	—	—	S	V _{DS} = 25V, I _D = 6.3A
Q _g	Total Gate Charge	—	17	26	nC	V _{DS} = 50V V _{GS} = 10V I _D = 6.3A
Q _{gs1}	Pre-V _{th} Gate-to-Source Charge	—	2.5	—		
Q _{gs2}	Post-V _{th} Gate-to-Source Charge	—	1.4	—		
Q _{gd}	Gate-to-Drain Charge	—	5.4	—		
Q _{godr}	Gate Charge Overdrive	—	7.7	—		
Q _{sw}	Switch Charge (Q _{gs2} + Q _{gd})	—	6.8	—		
Q _{oss}	Output Charge	—	5.9	—	nC	V _{DS} = 16V, V _{GS} = 0V
R _G	Gate Resistance	—	3.8	—	Ω	
t _{d(on)}	Turn-On Delay Time	—	5.0	—	ns	V _{DD} = 50V, V _{GS} = 10V I _D = 6.3A R _G = 1.8Ω
t _r	Rise Time	—	5.8	—		
t _{d(off)}	Turn-Off Delay Time	—	16	—		
t _f	Fall Time	—	5.1	—		
C _{iss}	Input Capacitance	—	760	—	pF	V _{GS} = 0V
C _{oss}	Output Capacitance	—	73	—		V _{DS} = 50V
C _{rss}	Reverse Transfer Capacitance	—	13	—		f = 1.0MHz

Avalanche Characteristics

	Parameter	Typ.	Max.
E _{AS}	Single Pulse Avalanche Energy ②	—	41
I _{AR}	Avalanche Current ①	—	6.3

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	11	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I _{SM}	Pulsed Source Current (Body Diode) ①	—	—	36		
V _{SD}	Diode Forward Voltage	—	—	1.3	V	T _J = 25°C, I _S = 6.3A, V _{GS} = 0V ③
t _{rr}	Reverse Recovery Time	—	47	71	ns	T _J = 25°C, I _F = 6.3A, V _{DD} = 50V
Q _{rr}	Reverse Recovery Charge	—	381	571	nC	di/dt = 500A/μs ③

Thermal Resistance

	Parameter	Typ.	Max.	Units
R _{θJC} (Bottom)	Junction-to-Case ④	—	4.3	°C/W
R _{θJC} (Top)	Junction-to-Case ④	—	40	
R _{θJA}	Junction-to-Ambient ⑤	—	45	
R _{θJA} (<10s)	Junction-to-Ambient ⑤	—	31	

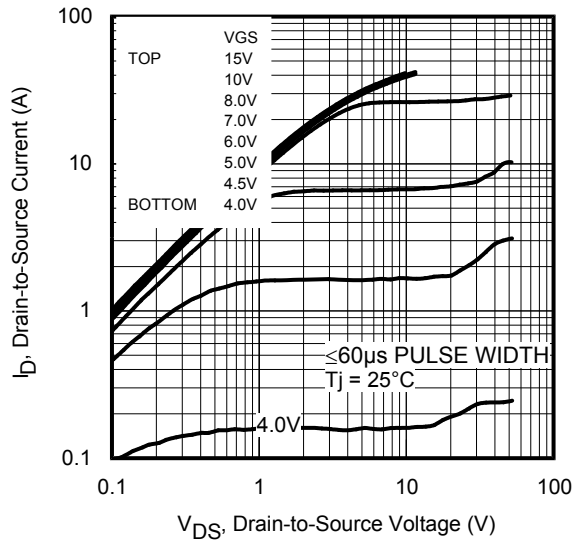


Fig 1. Typical Output Characteristics

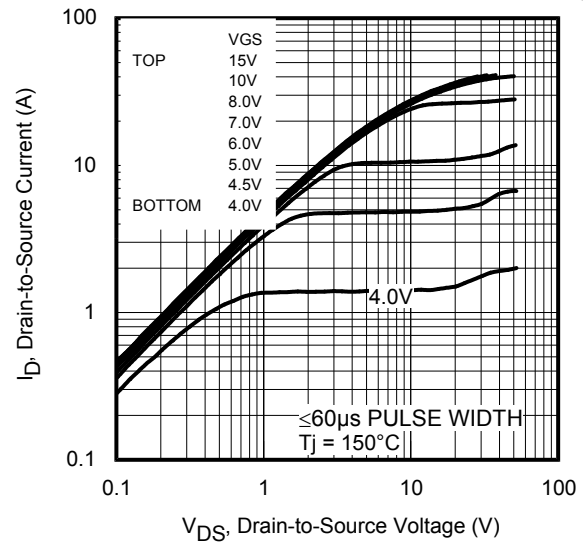


Fig 2. Typical Output Characteristics

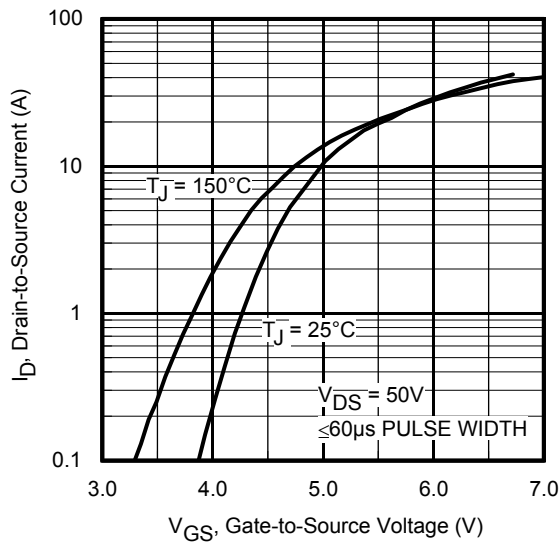


Fig 3. Typical Transfer Characteristics

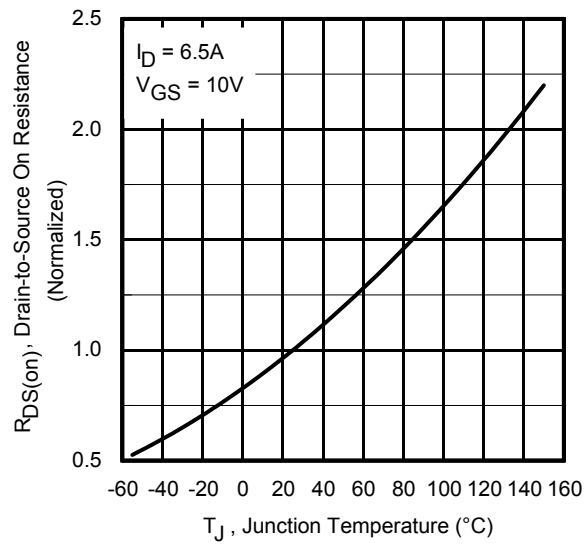


Fig 4. Normalized On-Resistance vs. Temperature

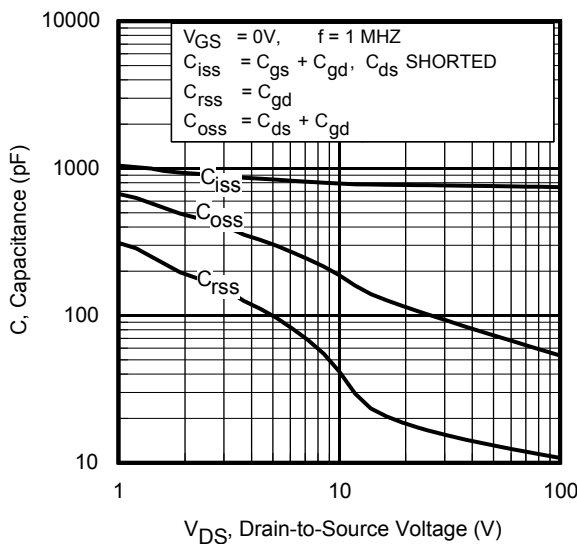


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

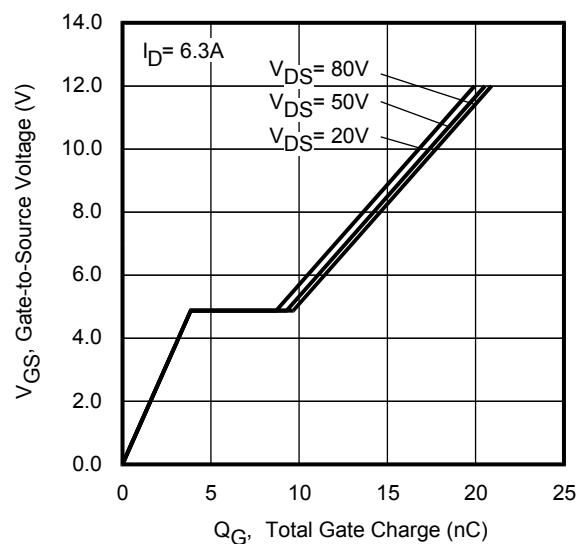
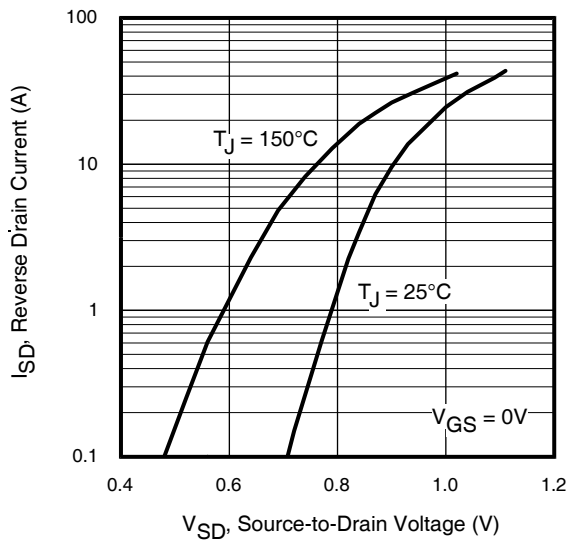
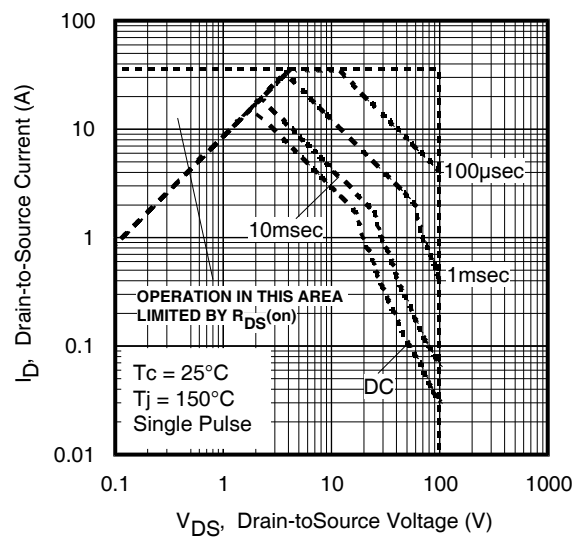
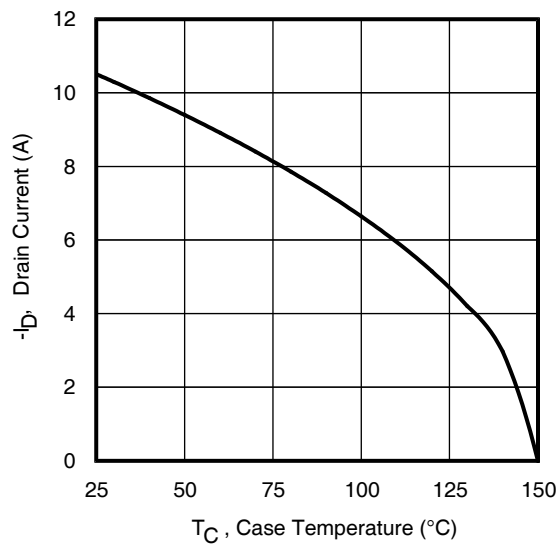
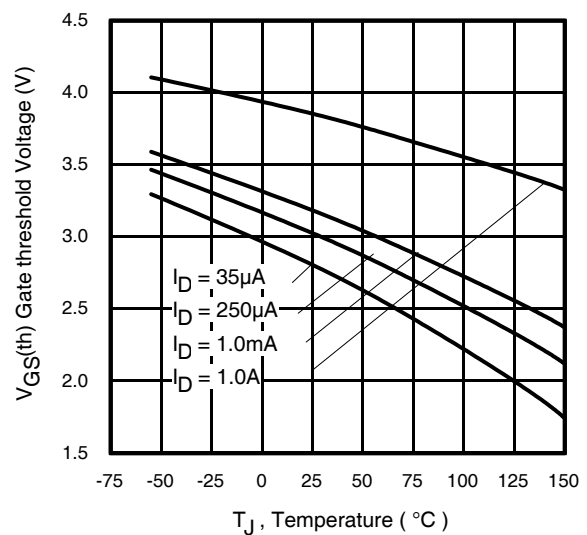
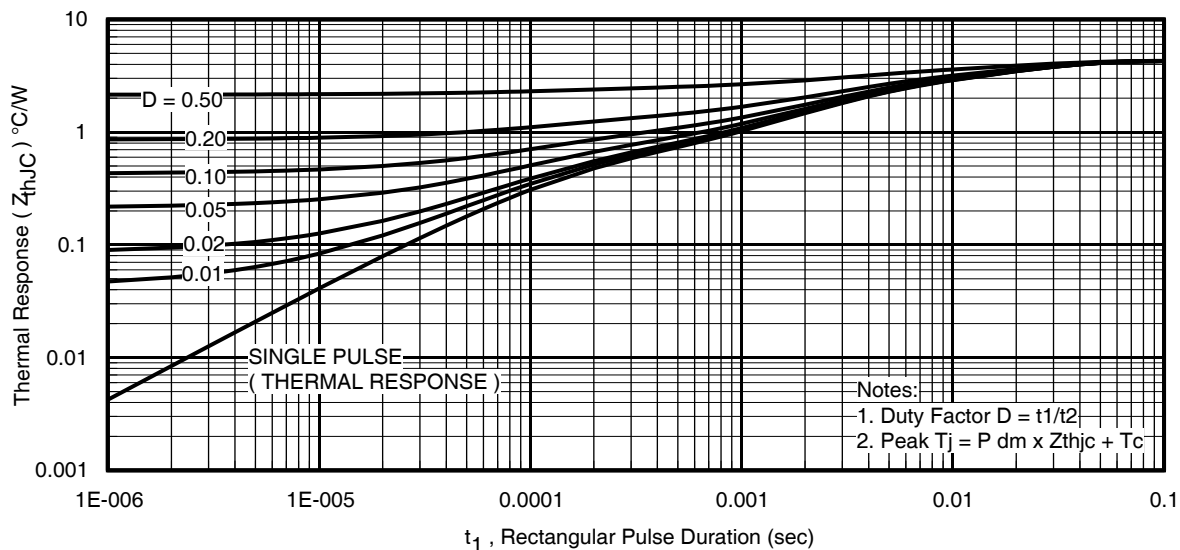


Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage


Fig 7. Typical Source-Drain Diode Forward Voltage

Fig 8. Maximum Safe Operating Area

Fig 9. Maximum Drain Current vs. Case Temperature

Fig 10. Drain-to-Source Breakdown Voltage

Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

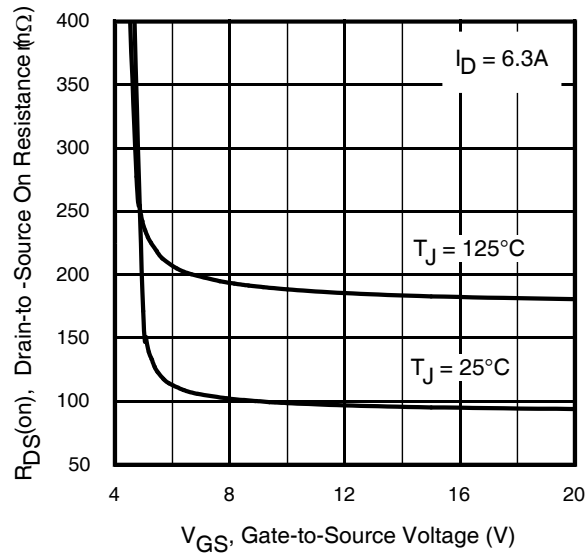


Fig 12. On-Resistance vs. Gate Voltage

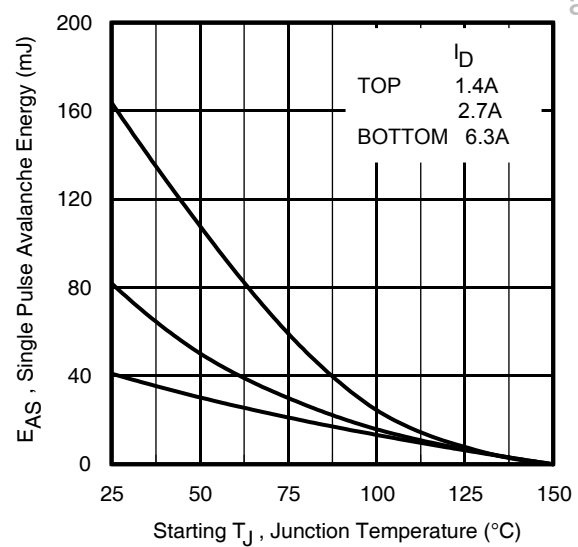


Fig 13. Maximum Avalanche Energy vs. Drain Current

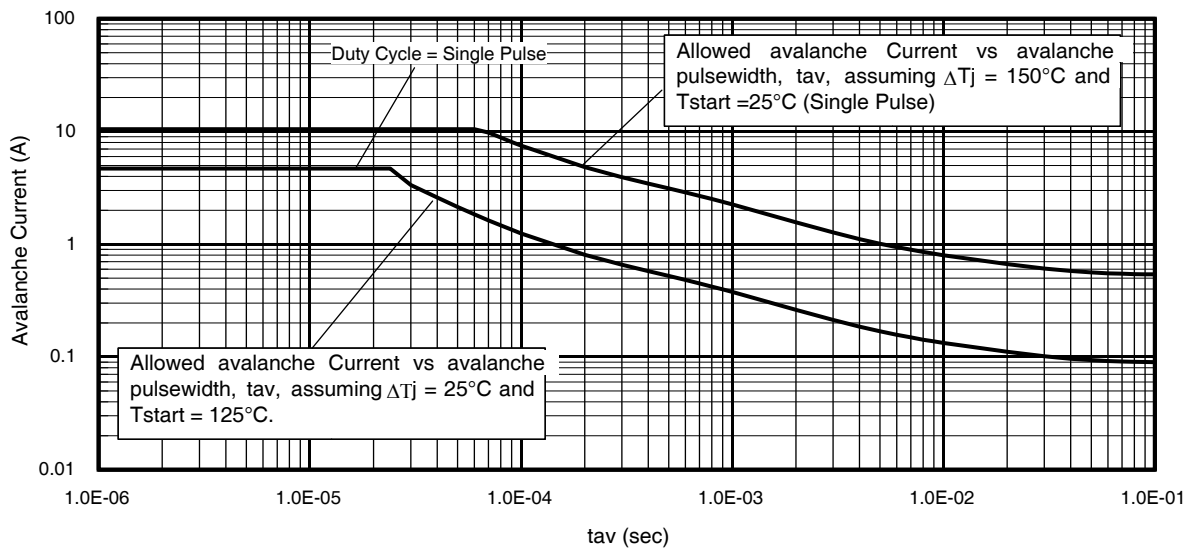


Fig 14. Typical Avalanche Current vs. Pulsewidth

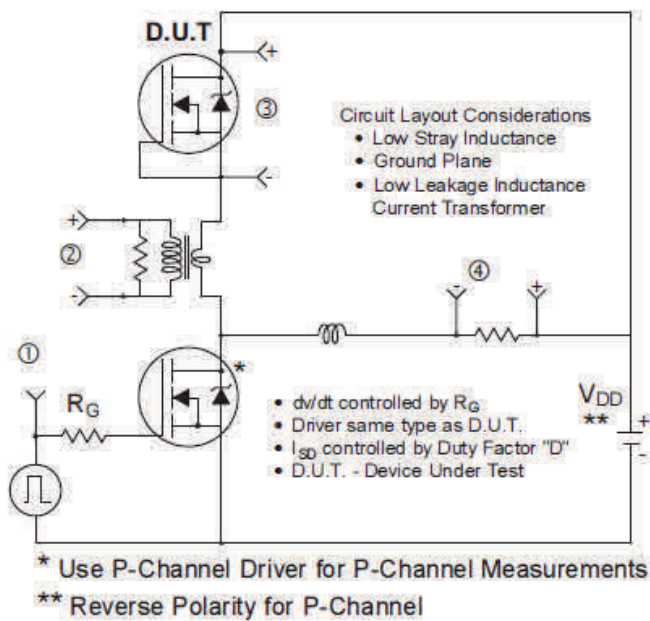


Fig 15. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

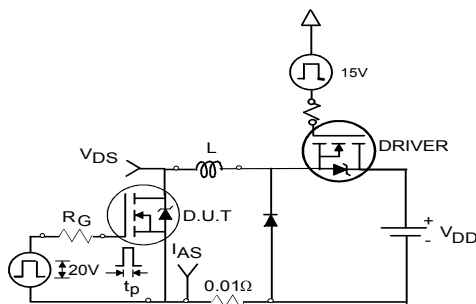


Fig 16a. Unclamped Inductive Test Circuit

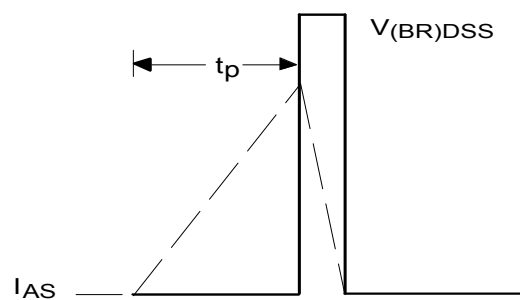


Fig 16b. Unclamped Inductive Waveforms

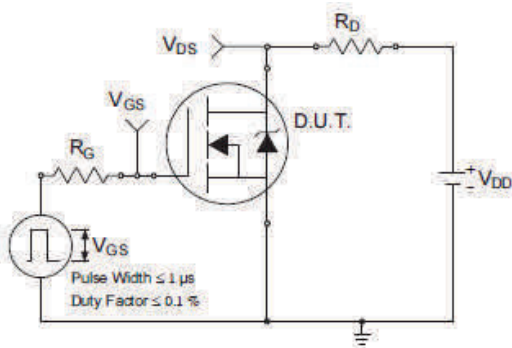


Fig 17a. Switching Time Test Circuit

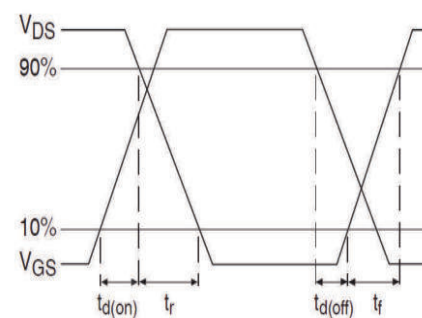


Fig 17b. Switching Time Waveforms

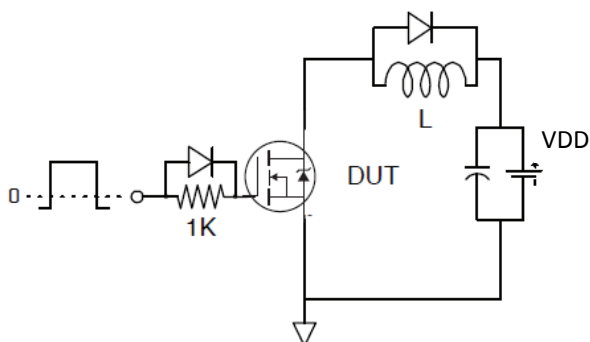


Fig 18. Gate Charge Test Circuit

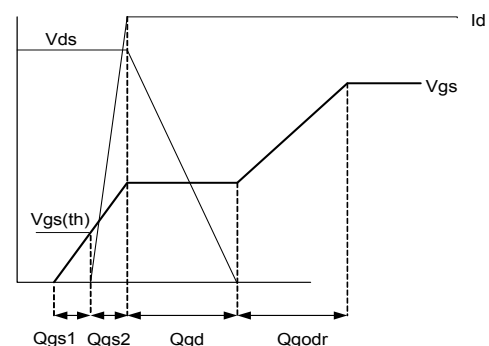
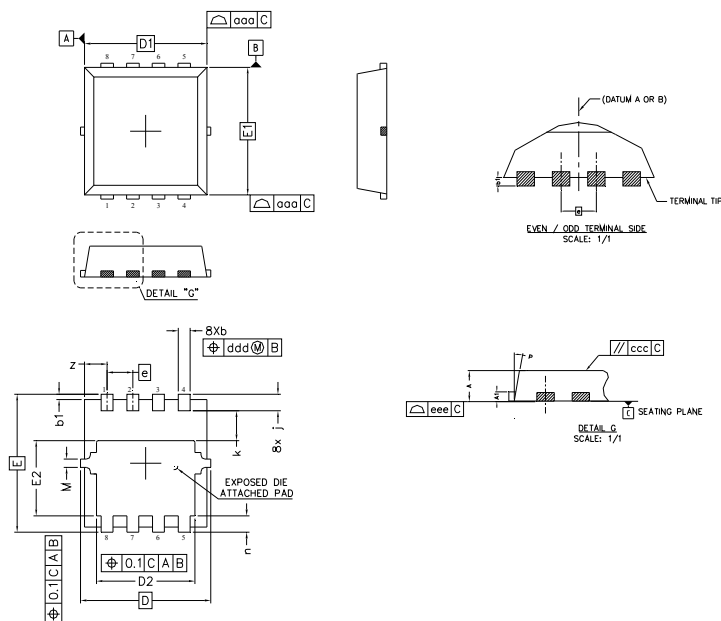


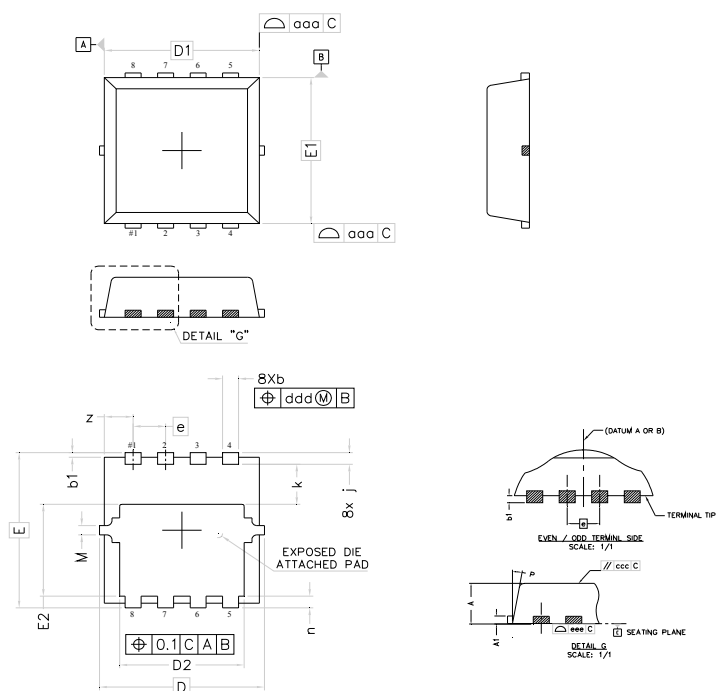
Fig 19. Gate Charge Waveform

PQFN 3.3 x 3.3 Outline “C” Package Details



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.70	0.80	.0276	.0315
A1	0.10	0.25	.0039	.0098
b	0.25	0.35	.0098	.0138
b1	0.05	0.15	.0020	.0059
D	3.20	3.40	.1260	.1339
D1	3.00	3.20	.1181	.1260
D2	2.39	2.59	.0941	.1020
E	3.25	3.45	.1280	.1358
E1	3.00	3.20	.1181	.1260
E2	1.78	1.98	.0701	.0780
e	0.65 BSC		.0255 BSC	
j	0.30	0.50	.0118	.0197
k	0.59	0.79	.0232	.0311
n	0.30	0.50	.0118	.0197
M	0.03	0.23	.0012	.0091
P	10°	12°	10°	12°
z	0.50	0.70	.0197	.0276

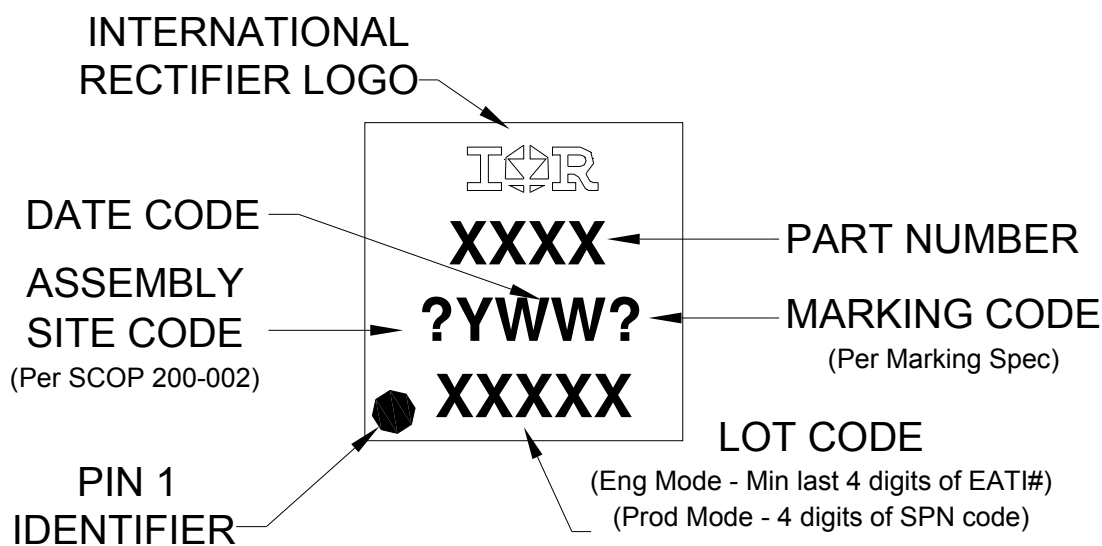
PQFN 3.3 x 3.3 Outline “G” Package Details



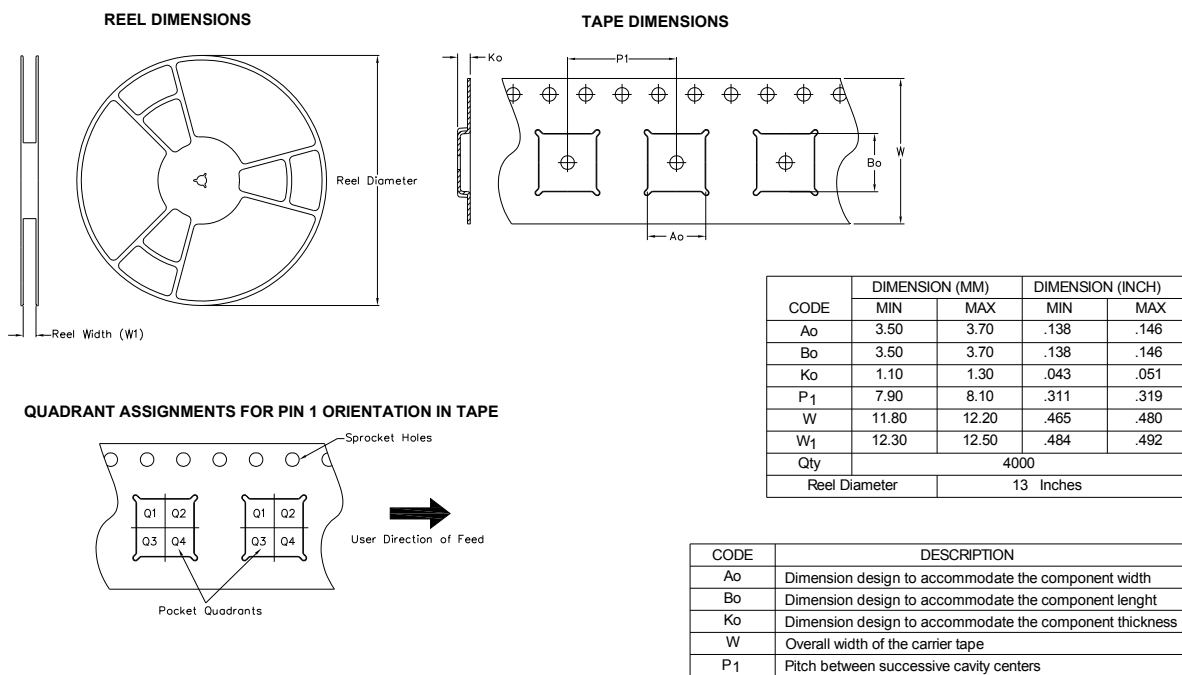
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.80	0.90	.0315	.0354
A1	0.12	0.22	.0047	.0086
b	0.22	0.42	.0087	.0165
b1	0.05	0.15	.0020	.0059
D	3.30 BSC		.1299 BSC	
D1	3.10 BSC		.1220 BSC	
D2	2.29	2.69	.0902	.1059
E	3.30 BSC		.1299 BSC	
E1	3.10 BSC		.1220 BSC	
E2	1.85	2.05	.0728	.0807
e	0.65 BSC		.0255 BSC	
j	0.15	0.35	.0059	.0137
k	0.75	0.95	.0295	.0374
n	0.15	0.35	.0059	.0137
M	NOM.	0.20	NOM.	.0078
P	9°	11°	9°	11°

For more information on board mounting, including footprint and stencil recommendation, please refer to application note AN-1136: <http://www.irf.com/technical-info/appnotes/an-1136.pdf>

For more information on package inspection techniques, please refer to application note AN-1154: <http://www.irf.com/technical-info/appnotes/an-1154.pdf>

PQFN 3.3 x 3.3 Part Marking


Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

PQFN 3.3 x 3.3 Tape and Reel


Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

Qualification Information[†]

Qualification Level	Industrial (per JEDEC JESD47F ^{††} guidelines)	
Moisture Sensitivity Level	PQFN 3.3mm x 3.3mm	MSL1 (per JEDEC J-STD-020D ^{††})
RoHS Compliant	Yes	

[†] Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/product-info/reliability>

^{††} Applicable version of JEDEC standard at the time of product release.

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^{\circ}\text{C}$, $L = 2.06\text{mH}$, $R_G = 50\Omega$, $I_{AS} = 6.3\text{A}$.
- ③ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.
- ④ R_{θ} is measured at T_J of approximately 90°C .
- ⑤ When mounted on 1 inch square PCB (FR-4). Please refer to AN-994 for more details:
<http://www.irf.com/technical-info/appnotes/an-994.pdf>
- ⑥ Calculated continuous current based on maximum allowable junction temperature.
- ⑦ Current is limited to 20A by source bonding technology.

Revision History

Date	Comments
6/5/2014	- Updated schematic on page 1 - Updated tape and reel on page 8
7/1/2014	Remove "SAWN" package outline on page 7.
2/23/2016	- Updated datasheet with corporate template - Updated package outline to reflect the PCN # (241-PCN30-Public) for "Option C" and "Option G" on page 7.

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